Ion-Implanted K-Band GaAs Power FET

G.C. Taylor, S.G. Liu and D. Bechtle. "Ion-Implanted K-Band GaAs Power FET." 1981 MTT-S International Microwave Symposium Digest 81.1 (1981 [MWSYM]): 46-48.

This paper reports the performance up to 26 GHz from a GaAs power FET produced by ion implantation. At 15 GHz, an output power of 250 mW at 3 dB gain with 27.4% power-added efficiency was obtained. At 26 GHz, 55 mW at 3 dB gain with 5% power-added efficiency was demonstrated. Capless annealing and a novel lift-off gate fabrication scheme was employed.

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